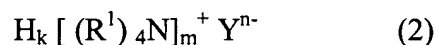
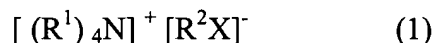


Amendments to the Claims:

1. (currently amended) A composition for forming porous film, the composition consisting essentially of siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2) :



wherein R^1 independently represents a straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent and R^1 's may be same or different; R^2 represents a hydrogen atom or an straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent; X represents CO_2 , OSO_3 or SO_3 ; Y represents SO_4 , SO_3 , CO_3 , O_2C-CO_2 , NO_3 or NO_2 ; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=1 and m=1, and wherein the one or more quaternary ammonium salts are present in an amount of 0.001 to 10 parts by weight per one part by weight of the siloxane polymer.

2. (original) The composition for forming porous film according to Claim 1 wherein said siloxane polymer has a weight-average molecular weight of 10,000 to 1,000,000 using polyethylene as a standard.

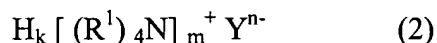
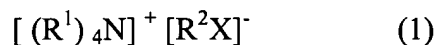
3. (previously presented) A method for forming porous film comprising steps of applying said composition of Claim 1 on a substrate to form a film and heating the film.

4. (previously presented) A porous film obtained from said composition of Claim 1.

5. (previously presented) An interlevel insulator film formed by said composition of Claim 1.

6. (currently amended) A semiconductor device comprising internal porous film which is formed by

applying on a substrate a composition for forming porous film consisting essentially of siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2):



wherein R^1 independently represents a straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent and R^1 s may be same or different; R^2 represents a hydrogen atom or an straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent; X represents CO_2 , OSO_3 or SO_3 ; Y represents SO_4 , SO_3 , CO_3 , O_2C-CO_2 , NO_3 or NO_2 ; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=1 and m=1, and wherein the one or more quaternary ammonium salts are present in an amount of 0.001 to 10 parts by weight per one part by weight of the siloxane polymer;

and heating.

7. (original) The semiconductor device according to Claim 6 wherein said siloxane polymer has a weight-average molecular weight between 10,000 and 1,000,000 using polyethylene as a standard.

8. (previously presented) The semiconductor device according to Claim 6 wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.